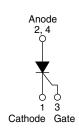
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Thyristor, Surface Mount, Phase Control SCR, 16 A



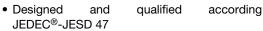


D²PAK (TO-263AB)

PRIMARY CHARACTERISTICS							
I _{T(AV)}	16 A						
V _{DRM} /V _{RRM}	800 V, 1200 V						
V_{TM}	1.25 V						
I _{GT}	45 mA						
T_J	-40 to +125 °C						
Package	D ² PAK (TO-263AB)						
Circuit configuration	Single SCR						

FEATURES

 Meets MSL level 1, per J-STD-020, LF maximum peak of 245 °C



ROHS COMPLIANT HALOGEN FREE

 Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

APPLICATIONS

- Input rectification (soft start)
- Vishay input diodes, switches and output rectifiers which are available in identical package outlines

DESCRIPTION

The VS-25TTS...S-M3 high voltage series of silicon controlled rectifiers are specifically designed for medium power switching and phase control applications. The glass passivation technology used has reliable operation up to 125 °C junction temperature.

OUTPUT CURRENT IN TYPICAL APPLICATIONS									
APPLICATIONS SINGLE-PHASE BRIDGE THREE-PHASE BRIDGE UNITS									
NEMA FR-4 or G10 glass fabric-based epoxy with 4 oz. (140 μm) copper	3.5	5.5							
Aluminum IMS, R _{thCA} = 15 °C/W	8.5	13.5	А						
Aluminum IMS with heatsink, R _{thCA} = 5 °C/W	16.5	25.0							

Note

• $T_A = 55$ °C, $T_J = 125$ °C, footprint 300 mm²

MAJOR RATINGS AND CHARACTERISTICS									
PARAMETER	TEST CONDITIONS	VALUES	UNITS						
I _{T(AV)}	Sinusoidal waveform	16	A						
I _{RMS}		25	A						
V_{RRM}/V_{DRM}		800 to 1200	V						
I _{TSM}		350	А						
V _T	16 A, T _J = 25 °C	1.25	V						
dV/dt		500	V/µs						
dl/dt		150	A/μs						
T _J		-40 to +125	°C						

VOLTAGE RATINGS									
PART NUMBER	V _{RRM} , MAXIMUM PEAK REVERSE VOLTAGE V	V _{DRM} , MAXIMUM PEAK DIRECT VOLTAGE V	I _{RRM} /I _{DRM} , AT 125 °C mA						
VS-25TTS08S-M3	800	800	10						
VS-25TTS12S-M3	1200	1200]						



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ABSOLUTE MAXIMUM RATINGS									
PARAMETER	SYMBOL	TEG	ST CONDITIONS	VAL	UES	UNITS			
PARAMETER	STIVIBUL	STRIBOL TEST CONDITIONS				UNITS			
Maximum average on-state current	I _{T(AV)}	T _C = 93 °C, 180° d	conduction half sine wave	16					
Maximum RMS on-state current	I _{RMS}			2	:5	Α			
Maximum peak, one-cycle,	,	10 ms sine pulse,	rated V _{RRM} applied	30	00	A			
non-repetitive surge current	I _{TSM}	10 ms sine pulse,	no voltage reapplied	3	50				
Marrian 124 for frain 1	l ² t	10 ms sine pulse,	rated V _{RRM} applied	4:	50	A ² s			
Maximum I ² t for fusing	I-t	10 ms sine pulse, no voltage reapplied			30	A ^z S			
Maximum I ² √t for fusing	I ² √t	t = 0.1 ms to 10 ms, no voltage reapplied			00	A ² √s			
Maximum on-state voltage drop	V_{TM}	16 A, T _J = 25 °C		1.25		V			
On-state slope resistance	r _t	T _{.1} = 125 °C		12.0		mΩ			
Threshold voltage	V _{T(TO)}	1) = 125 C		1.0		V			
Maximum various and direct leakage current	1 //	T _J = 25 °C	\/ reted\/ \/	0	.5				
Maximum reverse and direct leakage current	I _{RM} /I _{DM}	T _J = 125 °C	V_R = rated V_{RRM}/V_{DRM}	10					
Holding current	I _H	VS-25TTS08, VS-25TTS12	Anode supply = 6 V, resistive load, initial $I_T = 1$ A, $I_J = 25$ °C	- 150		mA			
Maximum latching current	ال	Anode supply = 6 V, resistive load, T _J = 25 °C			00				
Maximum rate of rise of off-state voltage	dV/dt	$T_J = T_J$ max., linear to 80 %, $V_{DRM} = R_g - k = open$			00	V/µs			
Maximum rate of rise of turned-on current	dl/dt	<u> </u>			150				

TRIGGERING									
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS					
Maximum peak gate power	P _{GM}		8.0	W					
Maximum average gate power	P _{G(AV)}		2.0	VV					
Maximum peak positive gate current	+ I _{GM}		1.5	Α					
Maximum peak negative gate voltage	- V _{GM}		10	V					
		Anode supply = 6 V, resistive load, T _J = - 10 °C	60						
Maximum required DC gate current to trigger	I _{GT}	Anode supply = 6 V, resistive load, T _J = 25 °C	45	mA					
		Anode supply = 6 V, resistive load, T _J = 125 °C	20						
		Anode supply = 6 V, resistive load, T _J = - 10 °C	2.5						
Maximum required DC gate voltage to trigger	V_{GT}	Anode supply = 6 V, resistive load, T _J = 25 °C	2.0	v					
		Anode supply = 6 V, resistive load, T _J = 125 °C	1.0	V					
Maximum DC gate voltage not to trigger	V_{GD}	T 105 °C V retadivelye	0.25						
Maximum DC gate current not to trigger	I_{GD}	T _J = 125 °C, V _{DRM} = rated value	2.0	mA					

SWITCHING									
PARAMETER SYMBOL TEST CONDITIONS VALUES UI									
Typical turn-on time	t _{gt}	T _J = 25 °C	0.9						
Typical reverse recovery time	t _{rr}	T = 125 °C	4	μs					
Typical turn-off time	turn-off time t_q $T_J = 125 ^{\circ}\text{C}$								

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THERMAL AND MECHANICAL SPECIFICATIONS									
PARAMETER SYMBOL TEST CONDITIONS VALUES UNI									
Maximum junction and storage temperature range	T _J , T _{Stg}		-40 to +125	°C					
Maximum thermal resistance, junction to case		DC operation	1.1	°C/W					
Typical thermal resistance, junction to ambient (PCB mount)			40	C/VV					
Approximate weight			2	g					
Approximate weight			0.07	OZ.					
Madriae daviae		Case style D ² PAK (TO-263AB)	25TTS08S						
Marking device		Case style D-PAN (10-263AB)	25TTS12S						

Note

⁽¹⁾ When mounted on 1" square (650 mm²) PCB of FR-4 or G-10 material 4 oz. (140 µm] copper 40 °C/W. For recommended footprint and soldering techniques refer to application note #AN-994

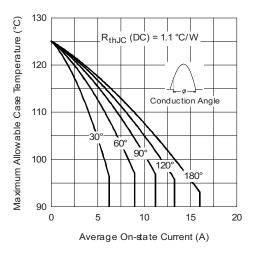


Fig. 1 - Current Rating Characteristics

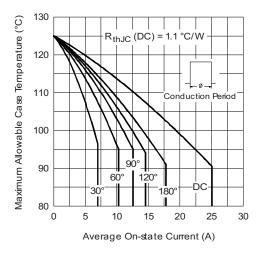


Fig. 2 - Current Rating Characteristics

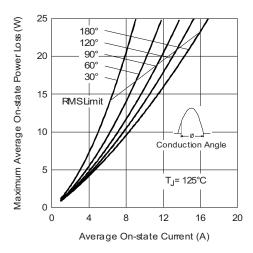


Fig. 3 - On-State Power Loss Characteristics

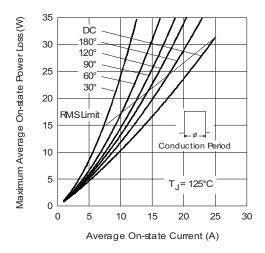


Fig. 4 - On-State Power Loss Characteristics

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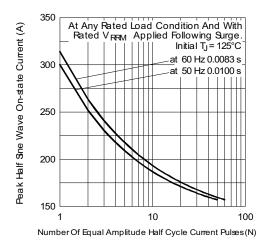


Fig. 5 - Maximum Non-Repetitive Surge Current

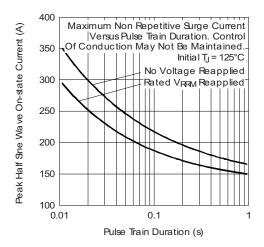


Fig. 6 - Maximum Non-Repetitive Surge Current

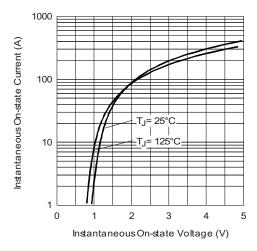


Fig. 7 - On-State Voltage Drop Characteristics

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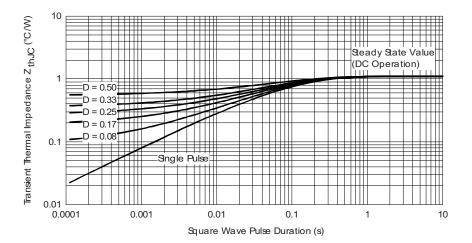


Fig. 8 - Gate Characteristics

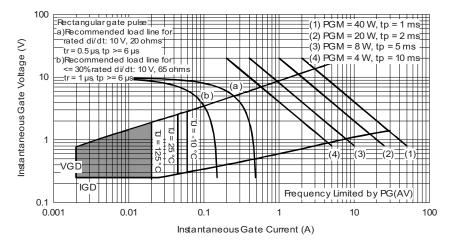
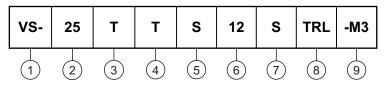


Fig. 9 - Thermal Impedance Z_{thJC} Characteristics

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ORDERING INFORMATION TABLE

Device code



- Vishay Semiconductors product
- 2 Current rating (25 = 25 A)
- Gircuit configuration:

 T = single thyristor
- 4 Package:
 - $T = D^2PAK (TO-263AB)$
- 5 Type of silicon:
- S = standard recovery rectifier 08 = 800 V

 Voltage rating: voltage code x 100 = V_{RRM} 12 = 1200 V
- 7 S = surface mountable
- 8 • None = tube
 - TRL = tape and reel (left oriented)
 - TRR = tape and reel (right oriented)
- 9 -M3 = halogen-free, RoHS-compliant, and terminations lead (Pb)-free

ORDERING INFORMATION (Example)									
PREFERRED P/N	BASE QUANTITY	PACKAGING DESCRIPTION							
VS-25TTS08S-M3	50	Antistatic plastic tubes							
VS-25TTS08STRL-M3	800	13" diameter plastic tape and reel							
VS-25TTS08STRR-M3	800	13" diameter plastic tape and reel							
VS-25TTS12S-M3	50	Antistatic plastic tubes							
VS-25TTS12STRL-M3	800	13" diameter plastic tape and reel							
VS-25TTS12STRR-M3	800	13" diameter plastic tape and reel							

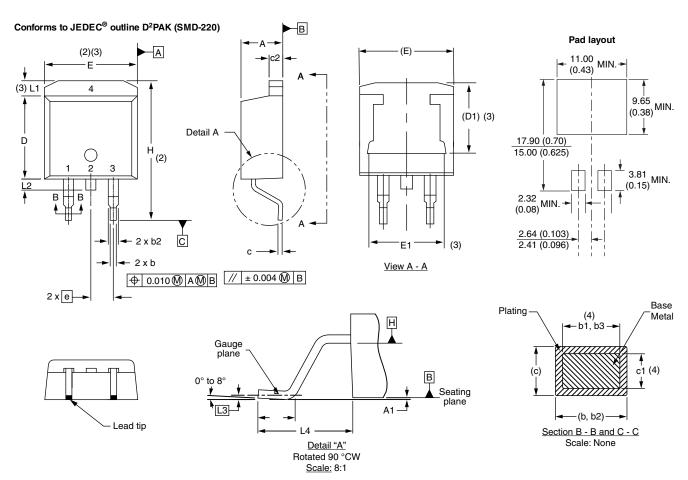
LINKS TO RELATED DOCUMENTS					
Dimensions www.vishay.com/doc?96164					
Part marking information	www.vishay.com/doc?95444				
Packaging information	www.vishay.com/doc?96424				



Vishay Semiconductors

D²PAK

DIMENSIONS in millimeters and inches



SYMBOL	MILLIMETERS		INC	HES	NOTES	NOTES	SYMBOL	MILLIM	ETERS	INC	HES	NOTES
STWIBOL	MIN.	MAX.	MIN.	MAX.	NOTES	NOTES	STWIDOL	MIN.	MAX.	MIN.	MAX.	NOTES
Α	4.06	4.83	0.160	0.190			D1	6.86	8.00	0.270	0.315	3
A1	0.00	0.254	0.000	0.010			E	9.65	10.67	0.380	0.420	2, 3
b	0.51	0.99	0.020	0.039			E1	7.90	8.80	0.311	0.346	3
b1	0.51	0.89	0.020	0.035	4		е	2.54	BSC	0.100	BSC	
b2	1.14	1.78	0.045	0.070			Н	14.61	15.88	0.575	0.625	
b3	1.14	1.73	0.045	0.068	4		L	1.78	2.79	0.070	0.110	
С	0.38	0.74	0.015	0.029			L1	-	1.65	-	0.066	3
c1	0.38	0.58	0.015	0.023	4		L2	1.27	1.78	0.050	0.070	
c2	1.14	1.65	0.045	0.065			L3	0.25	BSC	0.010	BSC	
D	8.51	9.65	0.335	0.380	2		L4	4.78	5.28	0.188	0.208	

Notes

- (1) Dimensioning and tolerancing per ASME Y14.5 M-1994
- (2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body
- (3) Thermal pad contour optional within dimension E, L1, D1 and E1
- (4) Dimension b1 and c1 apply to base metal only
- (5) Datum A and B to be determined at datum plane H
- (6) Controlling dimension: inches
- (7) Outline conforms to JEDEC® outline TO-263AB

Revision: 13-Jul-17 Document Number: 96164



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